BT131W series

GENERAL DESCRIPTION

Passivated, sensitive gate triacs in a plastic envelope suitable for surface mounting, intended for use in general

purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

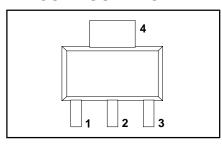
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BT131W- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500 500 1 12.5	600 600 1 12.5	V A A

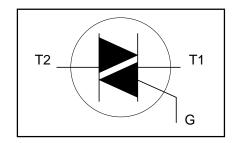
PINNING - SOT223

PIN DESCRIPTION	
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages			-500 500 ¹	-600 600 ¹	\ \
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge	-	1		A
		t = 20 ms t = 16.7 ms	-		2.5 3.8	A A A ² s
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 10 ms $I_{TM} = 1.5 \text{ A}; I_{G} = 0.2 \text{ A};$ $dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-	0	.5	
	triggering	T2+ G+ T2+ G- T2- G-	-	5 5	0 0 0	A/μs A/μs A/μs
I _{GM} V _{GM} P _{GM}	Peak gate current Peak gate voltage Peak gate power	T2- G+	-	2	0 <u>2</u> 5	A/μs A V W
P _{G(AV)} T _{stg} T _j	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -	0 1	.5 50 25	ĴĴ.

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/µs.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th i-sp}	Thermal resistance	full or half cycle	-	-	15	K/W
, , ,	junction to solder point		-	-	-	K/W
R _{th i-a}		pcb mounted; minimum footprint	-	156	-	K/W
,	junction to ambient	pcb mounted; pad area as in fig:14	-	70	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
		~ ' '	Γ2+ G+	-	0.4	3	mΑ
		· · · · · · · · · · · · · · · · · · ·	Γ2+ G-	-	1.3	3 3	mΑ
			Г2- G- 📗	-	1.4		mΑ
			Γ2- G+	-	3.8	7	mΑ
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
			Γ2+ G+	-	1.2	5	mΑ
		· ·	Г2+ G-	-	4.0	8	mΑ
			Г2- G- 📗	-	1.0	8 5 8	mΑ
		· ·	Γ2- G+	-	2.5		mΑ
l _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	1.3	5	mΑ
V _T	On-state voltage	$I_{T} = 1.4 \text{ A}$		-	1.2	1.5	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		-	0.7	1.5	V
		$ V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; I_i = 125 \text{ C}$	C	0.2	0.3	-	V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$, $T_j = 125$ °C		-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform; $R_{GK} = 1 k\Omega$	10	20	-	V/μs
	Critical rate of change of commutating voltage	$V_{DM} = 400 \text{ V; } T_j = 125 \text{ °C;}$ $dI_{com}/dt = 0.5 \text{ A/ms}$	2	-	-	V/μs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; $ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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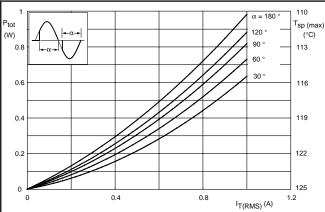


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

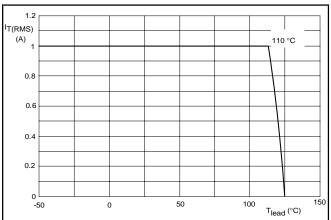


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus solder point temperature $T_{\rm sp}$.

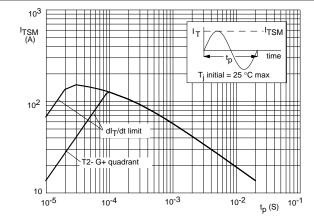


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

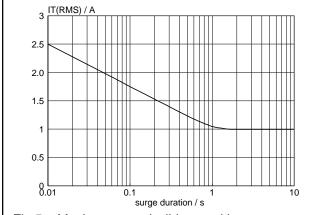


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{lead} \le 110$ °C.

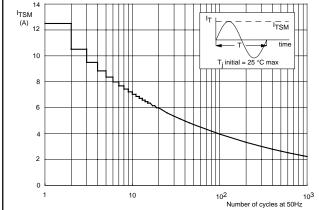


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

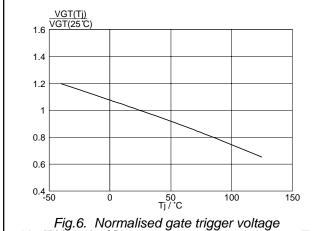
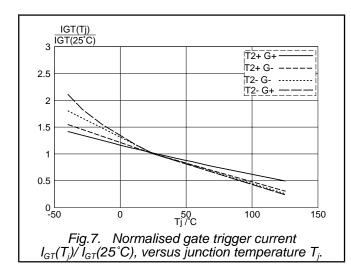


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

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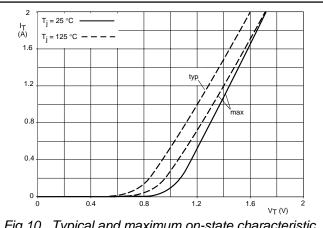


Fig. 10. Typical and maximum on-state characteristic.

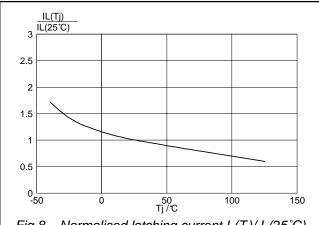


Fig.8. Normalised latching current $I_L(T_j)/I_L(25^{\circ}\text{C})$, versus junction temperature T_j .

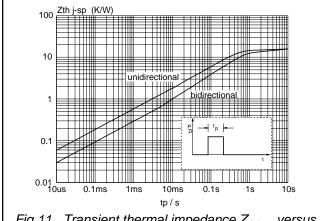


Fig.11. Transient thermal impedance $Z_{th i-sp}$, versus pulse width $t_{\rm p}$.

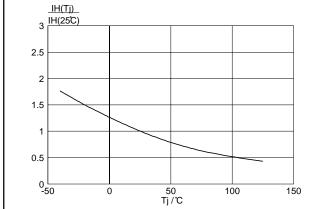


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}\text{C})$, versus junction temperature T_j .

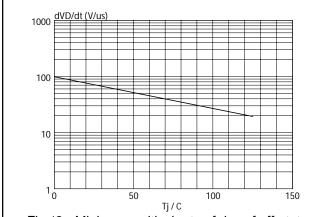
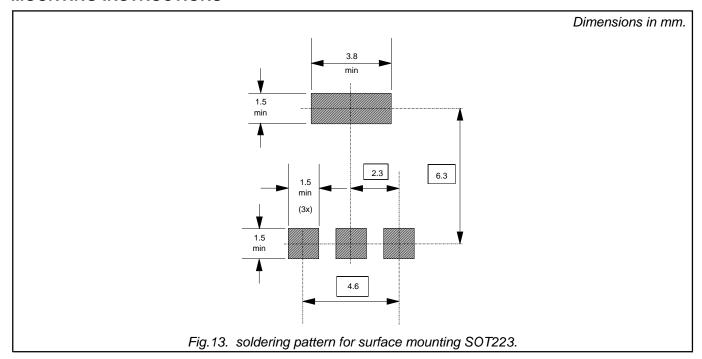


Fig.12. Minimum, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_i.

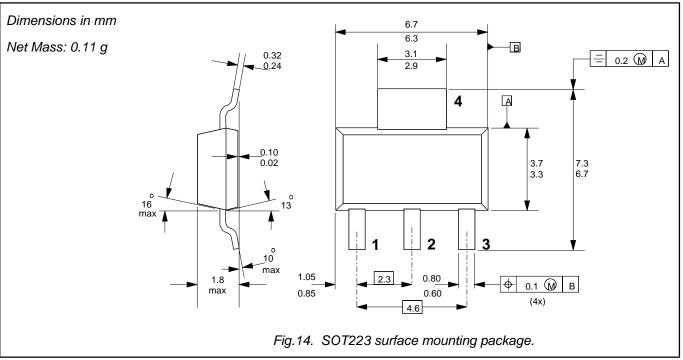
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MOUNTING INSTRUCTIONS



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MECHANICAL DATA



Notes

- For further information, refer to Philips publication SC18 " SMD Footprint Design and Soldering Guidelines".
 Order code: 9397 750 00505.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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